



# 80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8 (Type K)

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 9)
80V	$3.9 \text{m}\Omega$ @ $V_{GS} = 10V$	100A
60V	$6m\Omega @ V_{GS} = 6V$	100A

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Test in Production Ensures More Reliable and Robust End Application
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON))</sub>, yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Switching
- Synchronous Rectification
- DC-DC Converters

#### **Mechanical Data**

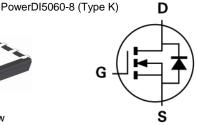
- Case: PowerDI<sup>®</sup>5060-8 (Type K)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



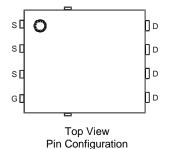




**Bottom View** 



Internal Schematic



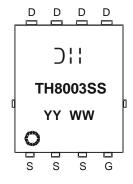
### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH8003SPS-13	PowerDI5060-8 (Type K)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



TH8003SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)

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# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	80	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	T <sub>C</sub> = +25°C (Note 9)	I <sub>D</sub>	100	А
	$T_{C} = +100^{\circ}C$		100	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	300	Α
Continuous Body Diode Forward Current (Note 6) T <sub>C</sub> = +25°C		Is	95	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	300	Α	
Avalanche Current, L = 3mH (Note 8)	I <sub>AS</sub>	15.8	Α	
Avalanche Energy, L = 3mH (Note 8)	E <sub>AS</sub>	375.4	mJ	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	65	Α	
Avalanche Energy, L = 0.1mH		Eas	211.4	mJ

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	2.9	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	51	°C/W
Total Power Dissipation (Note 6)	$P_{D}$	125	W
Thermal Resistance, Junction to Case (Note 6)	R <sub>0</sub> JC	1.2	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

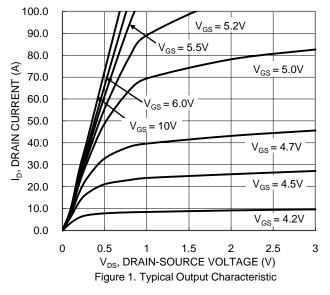
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 64V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	_	4	٧	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		I	3.1	3.9	mΩ	$V_{GS} = 10V, I_D = 30A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	4.1	6	mΩ	$V_{GS} = 6V, I_D = 30A$	
Diode Forward Voltage	$V_{SD}$	_	_	1.3	V	$V_{GS} = 0V, I_{S} = 30A$	
DYNAMIC CHARACTERISTICS (Note 8)						·	
Input Capacitance	C <sub>iss</sub>		8,952	_		V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	533	_	pF		
Reverse Transfer Capacitance	Crss	_	26	_			
Gate Resistance	$R_g$	_	0.85	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	124.3	_			
Gate-Source Charge	Q <sub>qs</sub>	_	24.3	_	nC	$V_{DS} = 40V$ , $I_{D} = 30A$ , $V_{GS} = 10V$	
Gate-Drain Charge	$Q_{qd}$		35.7	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	12.6	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 30A, R_{q} = 2.5\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	24.4	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>		47.9	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	20.9	_		J.	
Reverse Recovery Time	t <sub>RR</sub>	_	56.2	_	ns	1 50A di/dt 400A/	
Reverse Recovery Charge	Q <sub>RR</sub>	_	118.7	_	nC	$I_F = 50A$ , di/dt = 100A/ $\mu$ s	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

9. Package limited.

<sup>6.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.





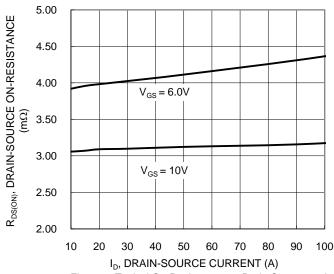


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

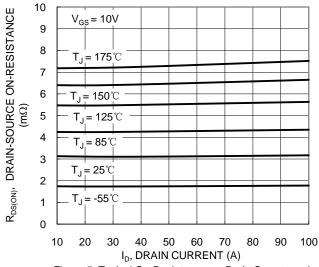
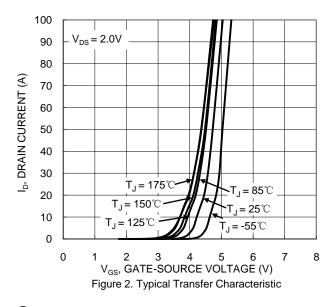


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



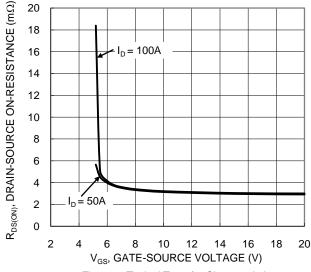


Figure 4. Typical Transfer Characteristic

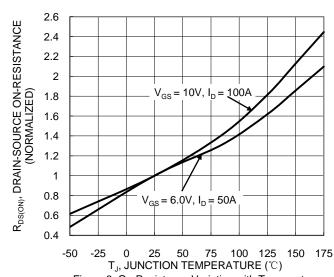


Figure 6. On-Resistance Variation with Temperature



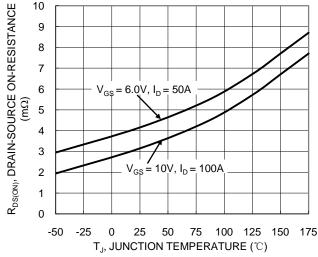
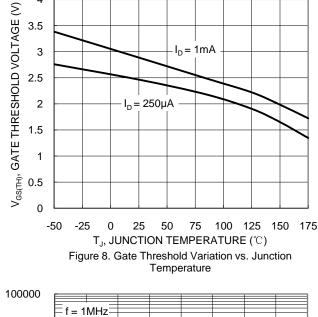
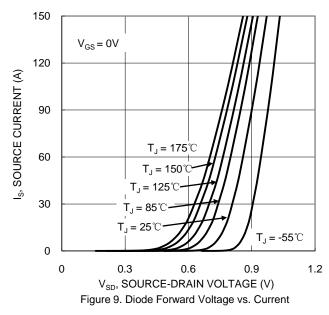
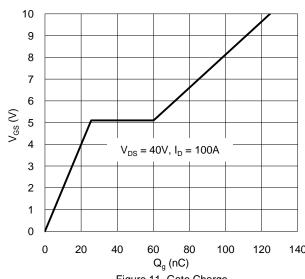


Figure 7. On-Resistance Variation with Temperature

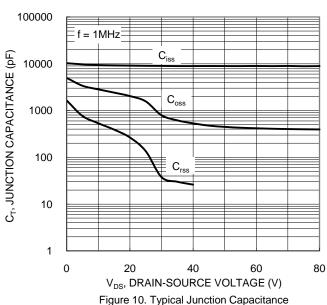


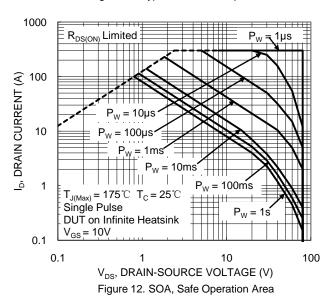
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140 Figure 11. Gate Charge







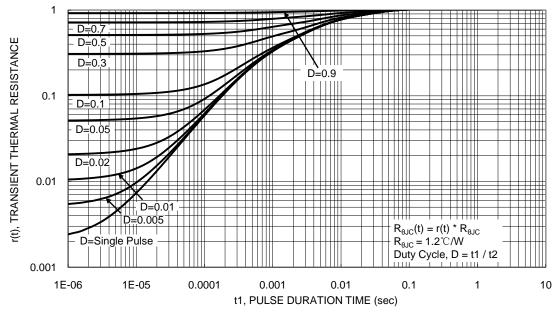


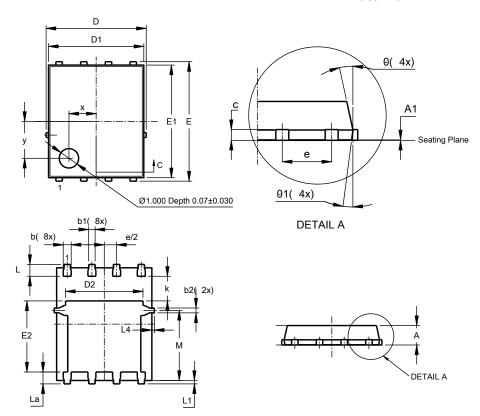
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)

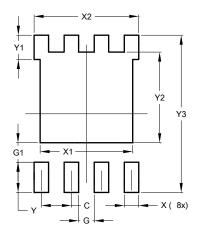


PowerDI <sup>®</sup> 5060-8 (Type K)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	5	.15 BS0			
D1	4.85	4.95	4.90		
D2	-	-	3.98		
Е	6.15 BSC				
E1	5.75	5.85	5.80		
E2	3.56	3.725	3.66		
е	1	.27BSC			
k	-	-	1.27		
L	0.51	0.71	0.61		
La	0.51	0.675	0.61		
L1	0.05	0.20	0.175		
L4	-	-	0.125		
М	3.50	3.71	3.605		
Х	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type K)



Dimensions	Value		
Diffictions	(in mm)		
С	1.270		
G	0.660		
G1	0.820		
Х	0.610		
X1	3.910		
X2	4.420		
Υ	1.270		
Y1	1.020		
Y2	3.810		
Y3	6.610		



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